

BAS70W SERIES SCHOTTKY DIODE

FEATURES

Power dissipation

$$P_D: 200 \text{ mW (} T_{amb}=25^\circ\text{C)}$$

Collector current

$$I_F: 70 \text{ mA}$$

Collector-base voltage

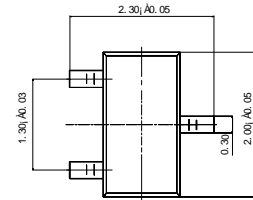
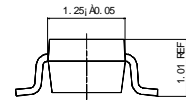
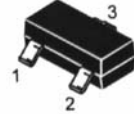
$$V_R: 70 \text{ V}$$

Operating and storage junction temperature range

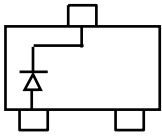
$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$

SOT-323

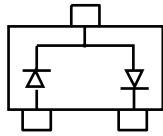
1. BASE
2. EMITTER
3. COLLECTOR



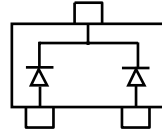
Unit: mm



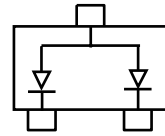
BAS70W Marking: K73



BAS70W-04 Marking: K74



BAS70W-05 Marking: K75



BAS70W-06 Marking: K76

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R = 10\mu\text{A}$	70		V
Reverse voltage leakage current	I_R	$V_R = 50\text{V}$		100	nA
Forward voltage	V_F	$I_F = 1\text{mA}$ $I_F = 15\text{mA}$		410 1000	mV
Diode capacitance	C_D	$V_R = 0\text{V}$, $f = 1\text{MHz}$		2	pF
Reveres recovery time	t_{rr}	$I_F = 10\text{mA}$ through $I_R = 10\text{mA}$ to $I_R = 1\text{mA}$		5	nS